

RJK1536DPE

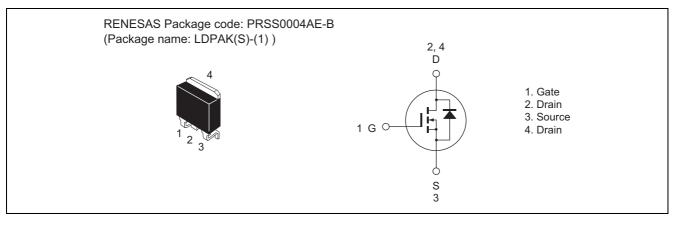
N-Channel Power MOSFET High-Speed Switching Use

> REJ03G1612-0200 Rev.2.00 Mar 11, 2008

Features

- V_{DSS}: 150 V
- R_{DS(on)}: 30 mΩ (Max)
- I_D: 50 A

Outline



Application

• Motor control, Lighting control, Solenoid control, DC-DC converter, etc.

Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
ltem	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	150	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	50	А
Drain peak current	I _{D (pulse)}	100	А
Body-drain diode reverse drain current	I _{DR}	50	А
Body-drain diode reverse drain peak current	I _{DR (pulse)}	100	А
Avalanche current	I _{AP} Note2	25	А
Channel dissipation	Pch Note1	125	W
Channel to case thermal impedance	θch-c	1.0	°C/W
Channel temperature	Tch	150	٥°
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. Value at $Tc = 25^{\circ}C$

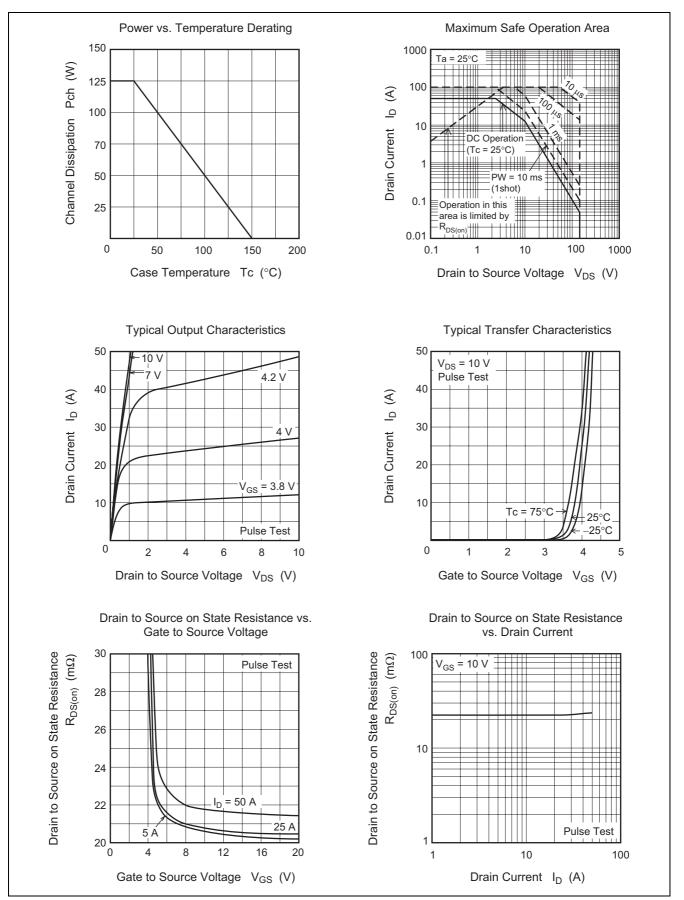
2. STch = 25° C, Tch $\leq 150^{\circ}$ C, L = 100μ H

Electrical Characteristics

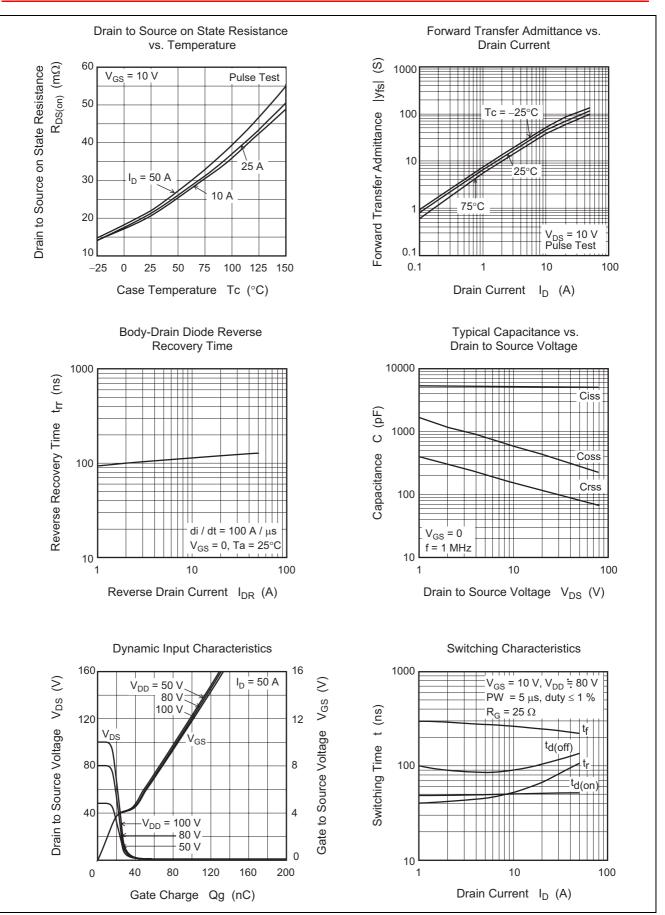
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	150	—	_	V	$I_{D} = 1 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	100	μΑ	$V_{DS} = 150 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	2.0	3.0	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}^{Note3}$
Static drain to source on state voltage	V _{DS(on)}	_	0.60	0.75	V	$I_D = 25 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
Static drain to source on state	R _{DS(on)}	_	24	30	mΩ	$I_D = 25 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
resistance						
Input capacitance	Ciss	_	5000	_	pF	$V_{DS} = 10 V$ $V_{GS} = 0$ $f = 1 MHz$
Output capacitance	Coss	—	560	—	pF	
Reverse transfer capacitance	Crss	_	165	_	pF	
Turn-on delay time	t _{d(on)}	_	50	_	ns	$V_{DD} = 80 V I_D = 25 A V_{GS} = 10 V R_G = 25 \Omega$
Rise time	tr	_	75	—	ns	
Turn-off delay time	t _{d(off)}	_	250	—	ns	
Fall time	t _f	_	100	_	ns	
Body-drain diode forward voltage	V _{DF}	_	0.9	1.5	V	I _F = 25 A, V _{GS} = 0
Body-drain diode reverse recovery time	t _{rr}	_	130	_	ns	$I_F = 50 \text{ A}, V_{GS} = 0$
						di _F /dt = 100 A/µs

Notes: 3. Pulse test

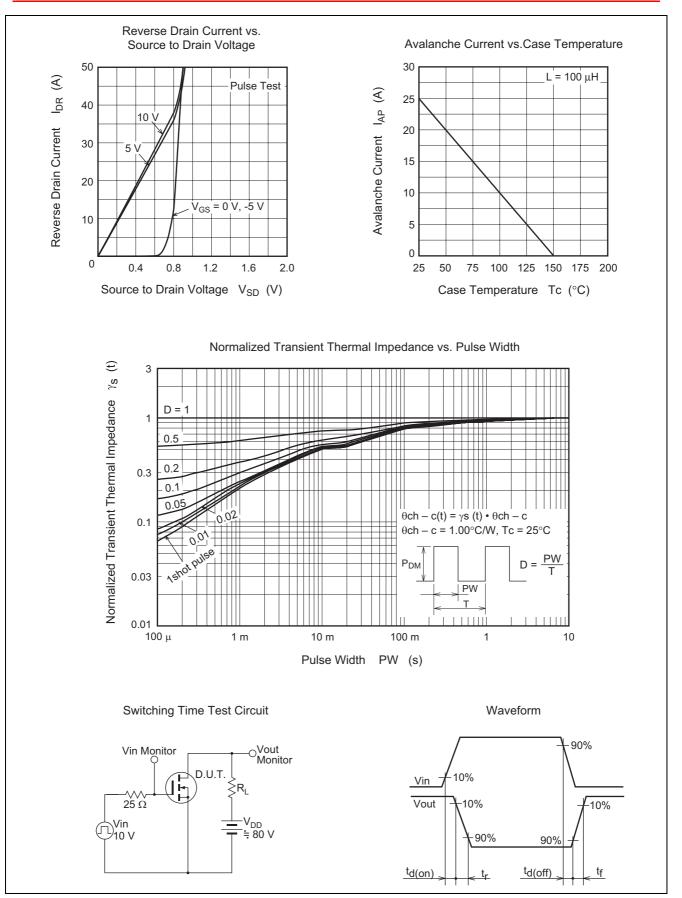
Main Characteristics



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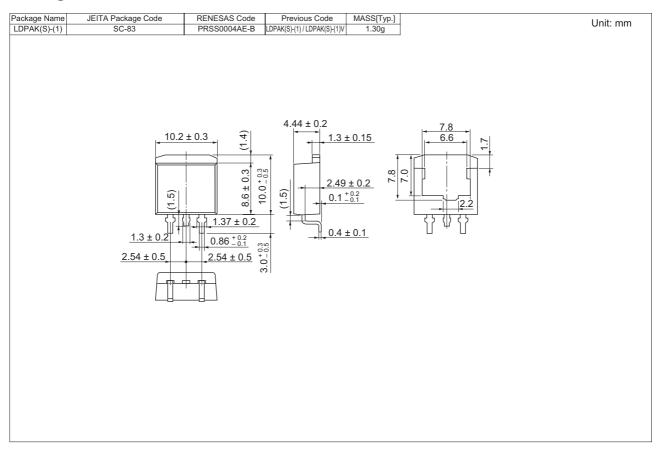


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Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK1536DPE-00-J3	1000 pcs	Taping

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